

[Supplemental] Highly Stable High Mobility Oxide Thin-Film Transistor with Gate Insulator Formed by N<sub>2</sub>O Plasma Treatment and Atomic-Layer Deposition

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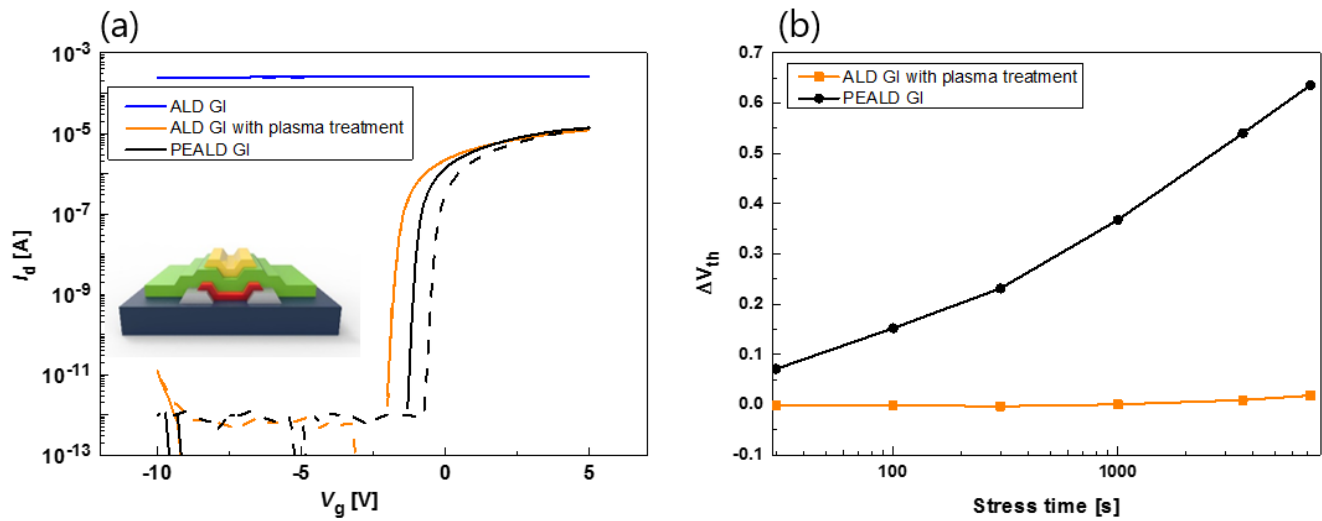


Figure 1 – (a) Transfer characteristics of the TFTs with ALD and PEALD GI without plasma treatment and plasma treated TFTs with ALD GI. (b) PBTS stability characteristics of the plasma treated TFTs with ALD GI and PEALD GI.